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(71) Applicant: NUTOOL, INC. [US/US]; 1645 McCandless Drive, Milpitas, CA 95035 (US).

(72) Inventors: UZOH, Cyprian, Emeka; 1645 McCandless Drive, Milpitas, CA 95035 (US). TALIEH, Homayoun; 2211 Bentley Ridge Drive, San Jose, CA 95138 (US).

(74) Agents: JAKOPIN, David, A. et al.; Pillsbury Madison & Sutro LLP, 1100 New York Avenue, N.W., Washington, DC 20005 (US).

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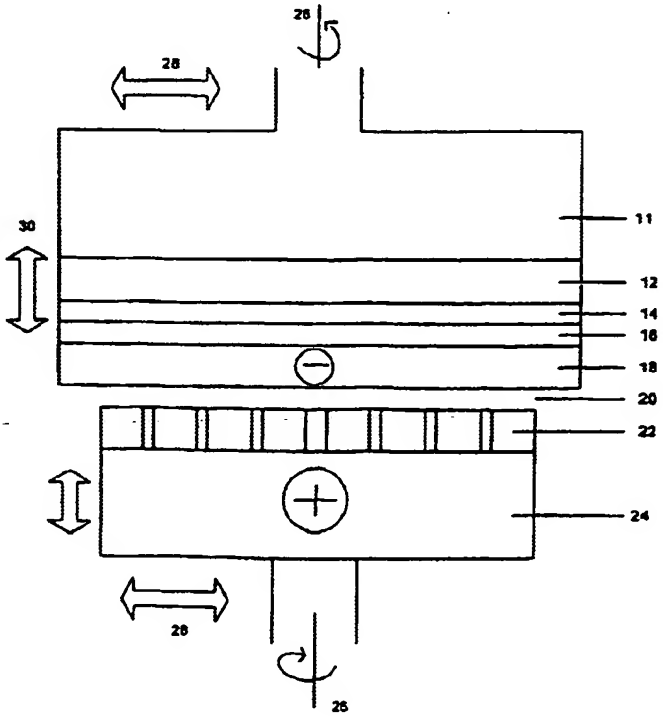
(54) Title: METHOD AND APPARATUS FOR DEPOSITING AND CONTROLLING THE TEXTURE OF A THIN FILM



(57) Abstract: The present invention provides a method and apparatus for plating a conductive material to a substrate and also modifying the physical properties of a conductive film (18b, 18c) while the substrate is being plated. The present invention further provides a method and apparatus that plates a conductive material on a workpiece surface in a "proximity" plating manner while a pad type material or other fixed feature is making contact with the workpiece surface in a "cold worked" manner. In this manner, energy stored in the cold worked regions (19b, 19c) of the plated layer is used to accelerate and enhance micro-structural recovery and growth. Thus, large grain size is obtained in the plated material at a lower annealing temperature and a shorter annealing time.

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